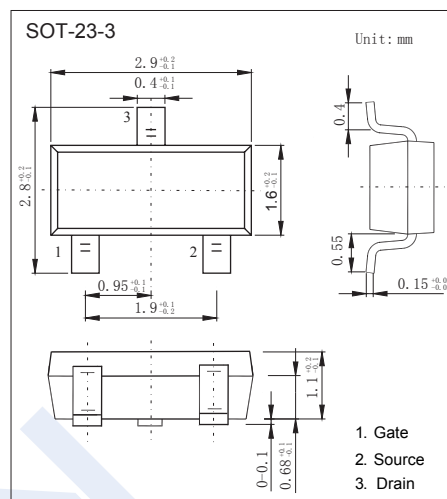
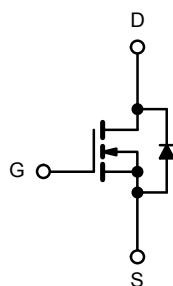


N-Channel MOSFET

SI2318CDS (KI2318CDS)

■ Features

- $V_{DS} (V) = 40V$
- $I_D = 5.6 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 42m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 51m\Omega$ ($V_{GS} = 4.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_c=25^\circ C$	I_D	5.6	A
	$T_c=70^\circ C$		4.5	
	$T_a=25^\circ C$		4.3	
	$T_a=70^\circ C$		3.5	
Pulsed Drain Current		I_{DM}	20	
Power Dissipation	$T_c=25^\circ C$	P_D	2.1	W
	$T_c=70^\circ C$		1.3	
	$T_a=25^\circ C$		1.25	
	$T_a=70^\circ C$		0.8	
Thermal Resistance.Junction- to-Ambient		R_{thJA}	100	$^\circ C/W$
Thermal Resistance.Junction- to-Foot		R_{thJF}	60	
Junction Temperature		T_J	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55 to 150	

N-Channel MOSFET

SI2318CDS (K12318CDS)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	40			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V			1	μA
		V _{DS} =40V, V _{GS} =0V, T _J =70°C			10	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2		2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =4.3A			42	mΩ
		V _{GS} =4.5V, I _D =3.9A			51	
On State Drain Current	I _{D(ON)}	V _{DS} ≥5V, V _{GS} =10V	20			A
Forward Transconductance	g _{FS}	V _{DS} =20V, I _D =4.3A		17		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =20V, f=1MHz		340		pF
Output Capacitance	C _{oss}			60		
Reverse Transfer Capacitance	C _{rss}			30		
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.6		6.6	Ω
Total Gate Charge	Q _g	V _{GS} =20V, V _{DS} =10V, I _D =4.3A		5.8	9	nC
		V _{GS} =20V, V _{DS} =4.5V, I _D =4.3A		2.9	6	
Gate Source Charge	Q _{gs}			1.1		
Gate Drain Charge	Q _{gd}			0.9		
Turn-On DelayTime	t _{d(on)}	V _{DD} = 20V, R _L = 5.7Ω I _D =3.5A, V _{GEN} = 4.5V, R _G = 1Ω		12	20	ns
Turn-On Rise Time	t _r			50	75	
Turn-Off DelayTime	t _{d(off)}			10	20	
Turn-Off Fall Time	t _f			8	16	
Turn-On DelayTime	t _{d(on)}	V _{DD} = 20V, R _L = 5.7Ω I _D =3.5A, V _{GEN} = 10V, R _G = 1Ω		7	14	ns
Turn-On Rise Time	t _r			20	30	
Turn-Off DelayTime	t _{d(off)}			14	21	
Turn-Off Fall Time	t _f			8	16	
Body Diode Reverse Recovery Time	t _{rr}	I _F =3.5A, dI/dt=100A/μs, T _J =25°C		15	23	nC
Body Diode Reverse Recovery Charge	Q _{rr}			7	14	
Reverse Recovery Fall Time	t _a			11		ns
Reverse Recovery Rise Time	t _b			4		
Maximum Body-Diode Continuous Current	I _S	T _C =25°C			1.75	A
Pulse Diode Forward Current	I _{SM}				20	
Diode Forward Voltage	V _{SD}	I _S =3.5A, V _{GS} =0V			1.2	V

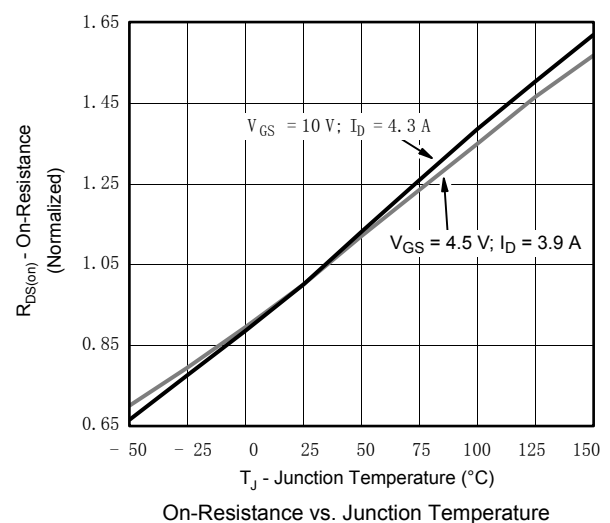
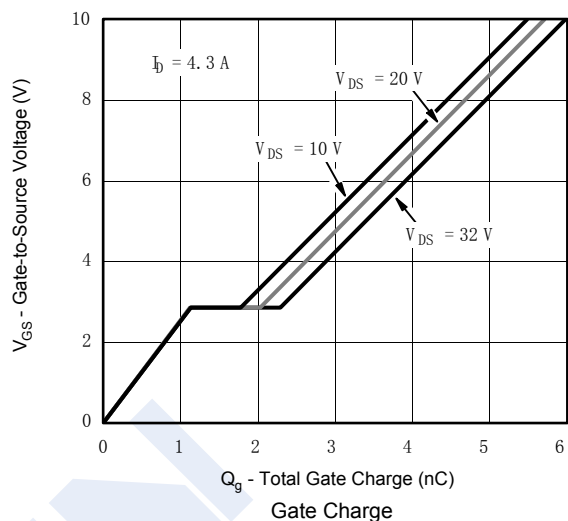
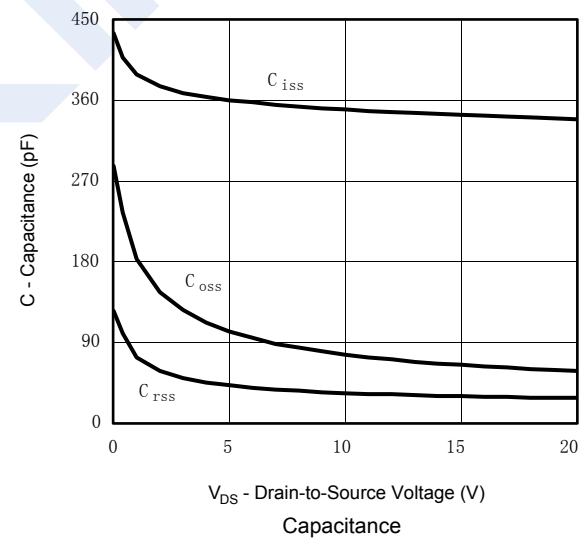
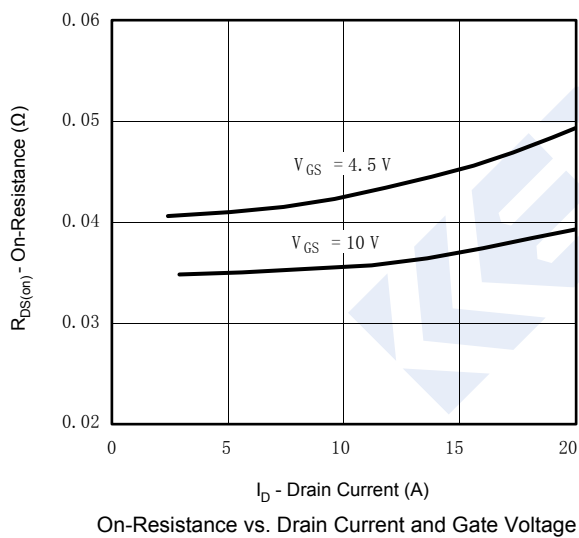
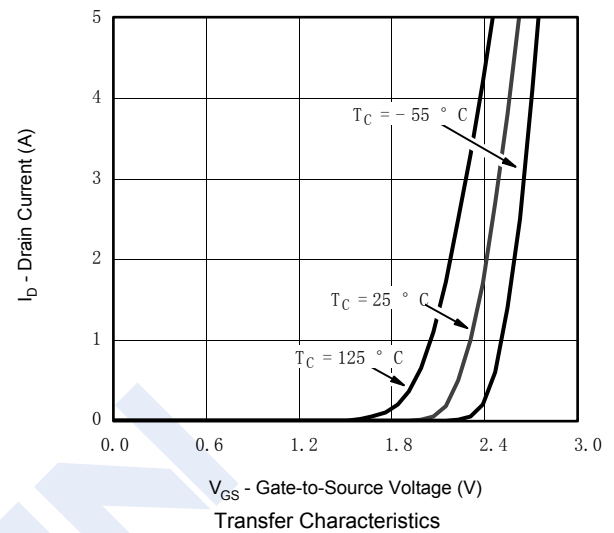
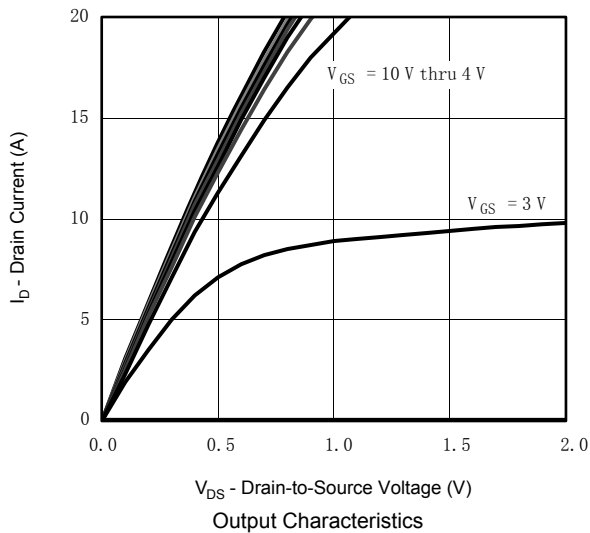
■ Marking

Marking	P9*
---------	-----

N-Channel MOSFET

SI2318CDS (KI2318CDS)

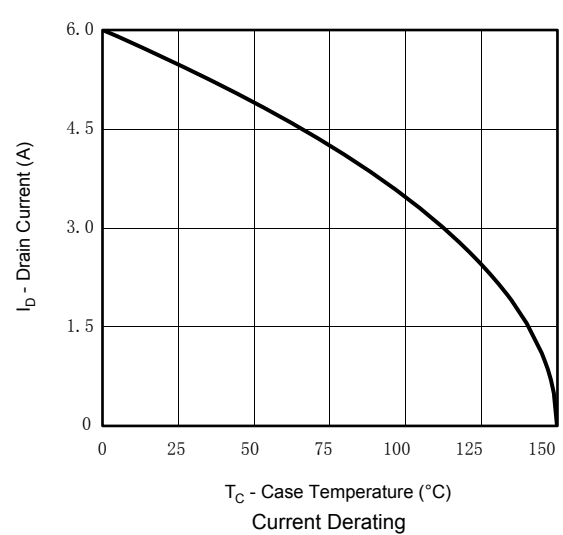
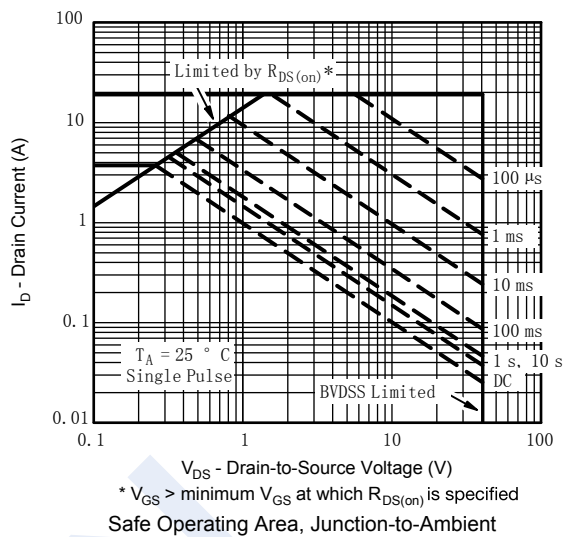
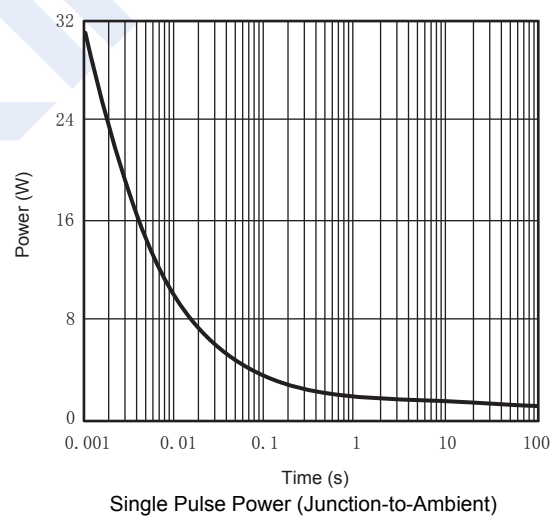
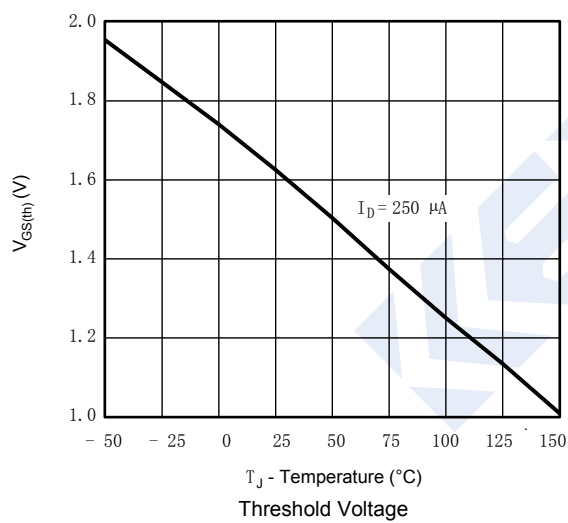
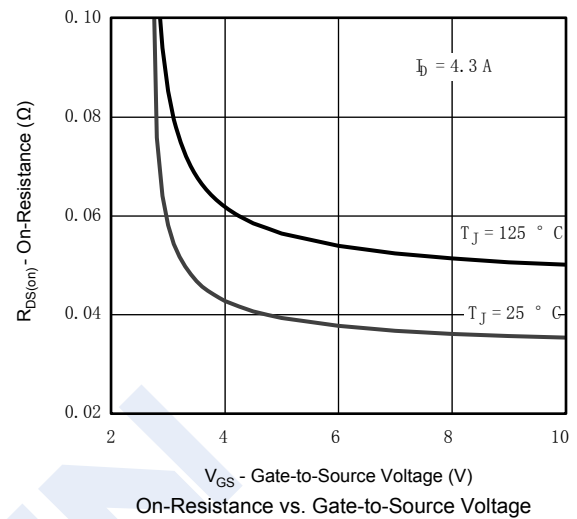
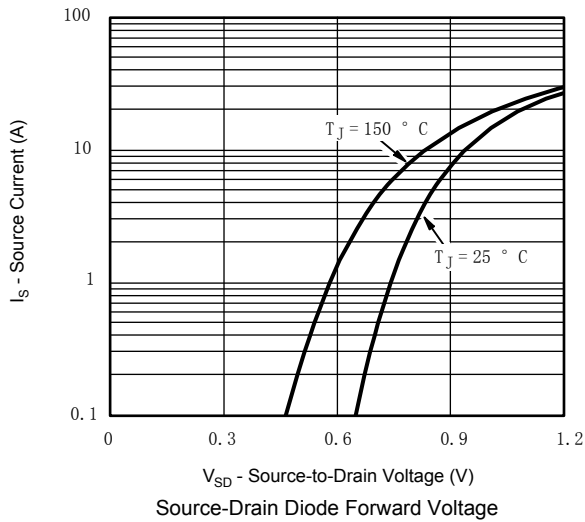
Typical Characteristics



N-Channel MOSFET

SI2318CDS (KI2318CDS)

Typical Characteristics



N-Channel MOSFET

SI2318CDS (K12318CDS)

Typical Characteristics

